

HiPerFRED²

$$V_{RRM} = 2 \times 400V$$

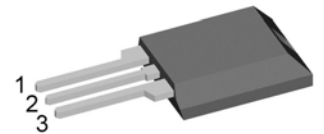
$$I_{FAV} = 10A$$

$$t_{rr} = 45ns$$


High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 Phase leg

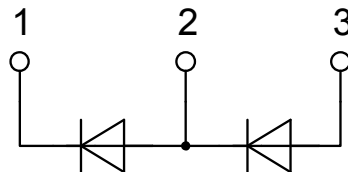
Part number

DPG10P400PJ



Backside: isolated

 E72873

**Features / Advantages:**

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

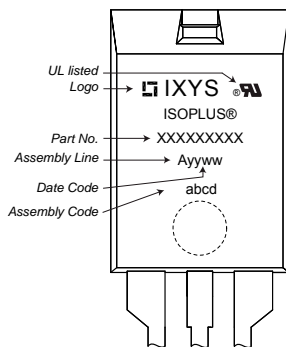
Package: ISOPLUS220

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

Fast Diode				Ratings		
Symbol	Definition	Conditions	min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			400	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			400	V
I_R	reverse current, drain current	$V_R = 400 V$	$T_{VJ} = 25^{\circ}C$		1	μA
		$V_R = 400 V$	$T_{VJ} = 150^{\circ}C$		0.18	mA
V_F	forward voltage drop	$I_F = 10 A$	$T_{VJ} = 25^{\circ}C$		1.28	V
					1.48	V
		$I_F = 10 A$	$T_{VJ} = 150^{\circ}C$		1.02	V
					1.24	V
I_{FAV}	average forward current	$T_C = 145^{\circ}C$ rectangular $d = 0.5$	$T_{VJ} = 175^{\circ}C$		10	A
V_{FO}	threshold voltage	} for power loss calculation only	$T_{VJ} = 175^{\circ}C$		0.78	V
r_F	slope resistance				19.4	m Ω
R_{thJC}	thermal resistance junction to case				2.5	K/W
R_{thCH}	thermal resistance case to heatsink			0.50		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}C$			60	W
I_{FSM}	max. forward surge current	$t = 10 ms; (50 Hz), sine; V_R = 0 V$	$T_{VJ} = 45^{\circ}C$		130	A
C_J	junction capacitance	$V_R = 200 V \quad f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		16	pF
I_{RM}	max. reverse recovery current	} $I_F = 15 A; V_R = 270 V$	$T_{VJ} = 25^{\circ}C$		4	A
			$T_{VJ} = 125^{\circ}C$		5.5	A
t_{rr}	reverse recovery time	} $-di_F/dt = 200 A/\mu s$	$T_{VJ} = 25^{\circ}C$		45	ns
			$T_{VJ} = 125^{\circ}C$		70	ns

Package ISOPLUS220		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			35	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				2		g
F_C	mounting force with clip		20		60	N
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	1.0			mm
$d_{Spbl/Apb}$		terminal to backside	3.0			mm
V_{ISOL}	isolation voltage	t = 1 second	3600			V
		t = 1 minute	3000			V

Product Marking



Part number

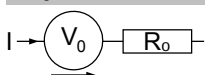
- D = Diode
- P = HiPerFRED
- G = extreme fast
- 10 = Current Rating [A]
- P = Phase leg
- 400 = Reverse Voltage [V]
- PJ = ISOPLUS220AB (3)

Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DPG10P400PJ	DPG10P400PJ	Tube	50	507202

Equivalent Circuits for Simulation

* on die level

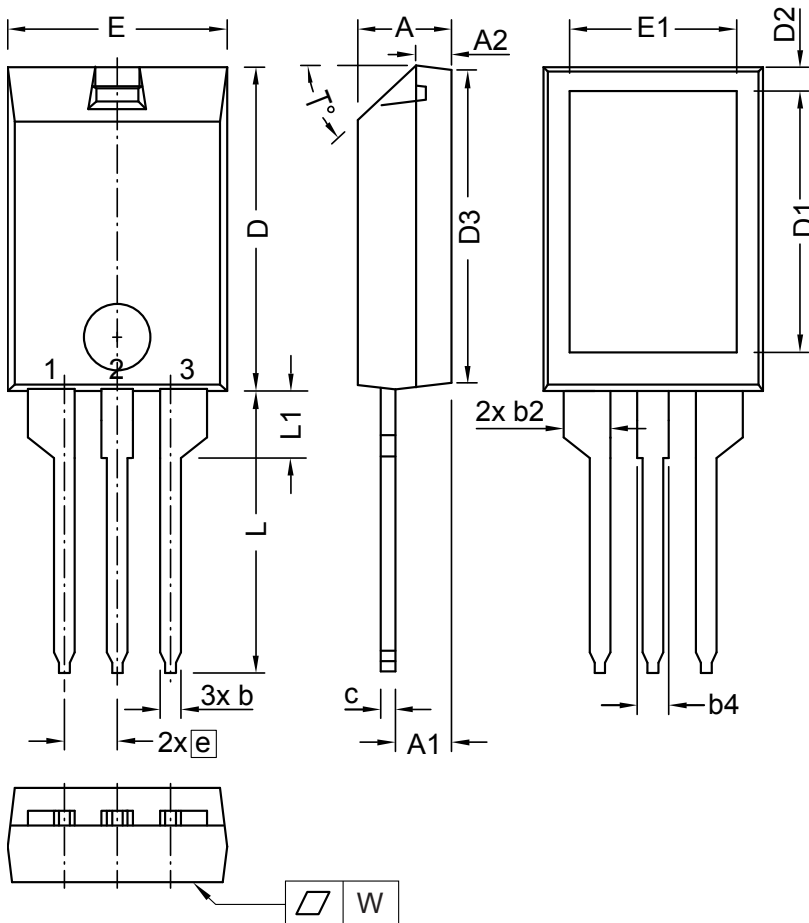
$T_{VJ} = 175\text{ °C}$



Fast Diode

$V_{0\max}$	threshold voltage	0.78	V
$R_{0\max}$	slope resistance *	16.2	mΩ

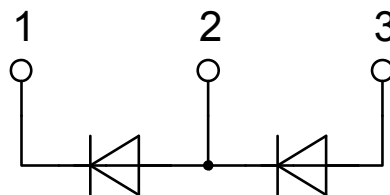
Outlines ISOPLUS220



Dim.	Millimeters		Inches	
	min	max	min	max
A	4.00	5.00	0.157	0.197
A1	2.50	3.00	0.098	0.118
A2	1.60	1.80	0.063	0.071
b	0.90	1.30	0.035	0.051
b2	2.35	2.55	0.093	0.100
b4	1.25	1.65	0.049	0.065
c	0.70	1.00	0.028	0.039
D	15.00	16.00	0.591	0.630
D1	12.00	13.00	0.472	0.512
D2	1.10	1.50	0.043	0.059
D3	14.90	15.50	0.587	0.610
E	10.00	11.00	0.394	0.433
E1	7.50	8.50	0.295	0.335
e	2.54 BSC		0.100 BSC	
L	13.00	14.50	0.512	0.571
L1	3.00	3.50	0.118	0.138
T°	42.5	47.5		
W	-	0.1	-	0.004

Die konvexe Form des Substrates ist typ. < 0.04 mm über der Kunststoffoberfläche der Bauteilunterseite
 The convex bow of substrate is typ. < 0.04 mm over plastic surface level of device bottom side

Die Gehäuseabmessungen entsprechen dem Typ TO-273 gemäß JEDEC außer D und D1.
 This drawing will meet all dimensions requirement of JEDEC outline TO-273 except D and D1.



Fast Diode

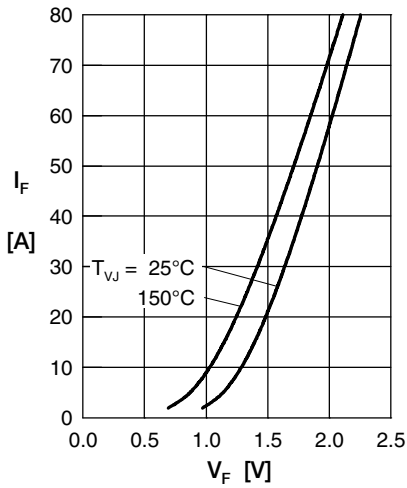


Fig. 1 Forward current I_F versus V_F

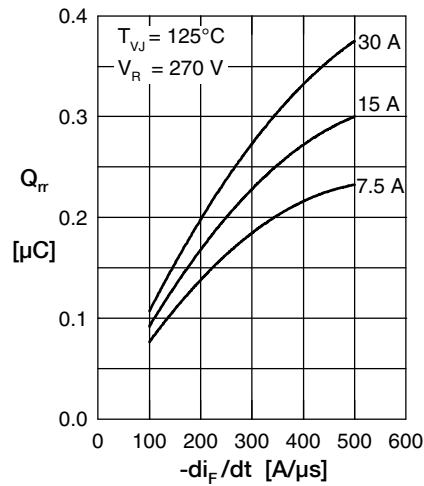


Fig. 2 Typ. reverse recov. charge Q_{rr} versus $-di_F/dt$

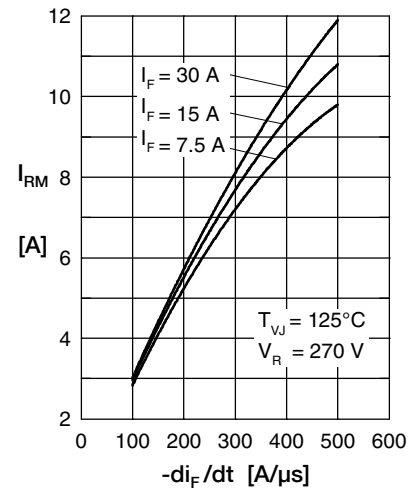


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

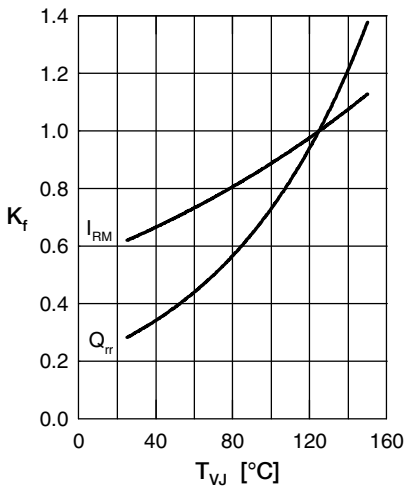


Fig. 4 Typ. dynamic parameters Q_{rr} , I_{RM} versus T_{VJ}

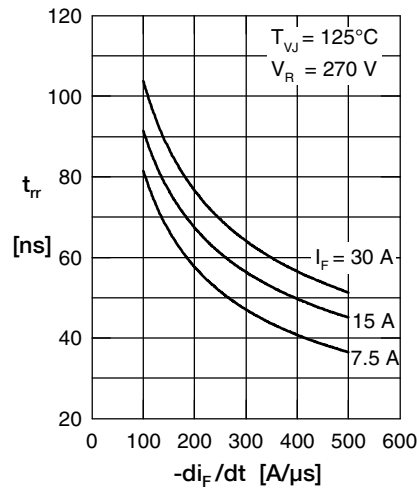


Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

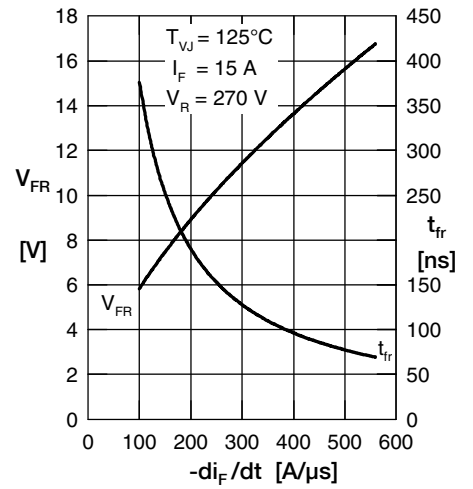


Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_F/dt

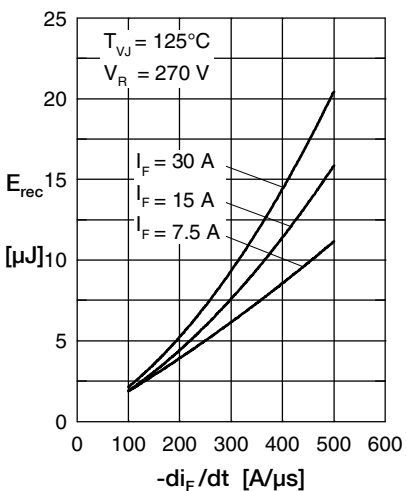


Fig. 7 Typ. recovery energy E_{rec} versus $-di_F/dt$

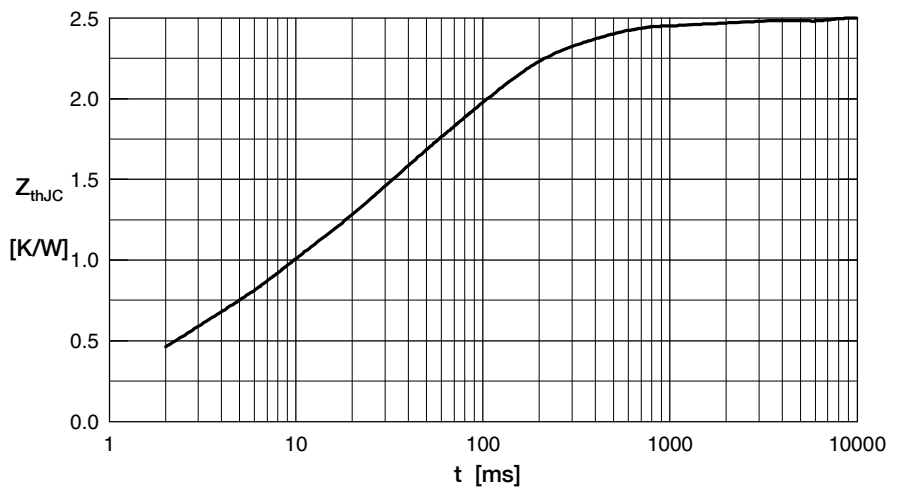


Fig. 8 Transient thermal resistance junction to case